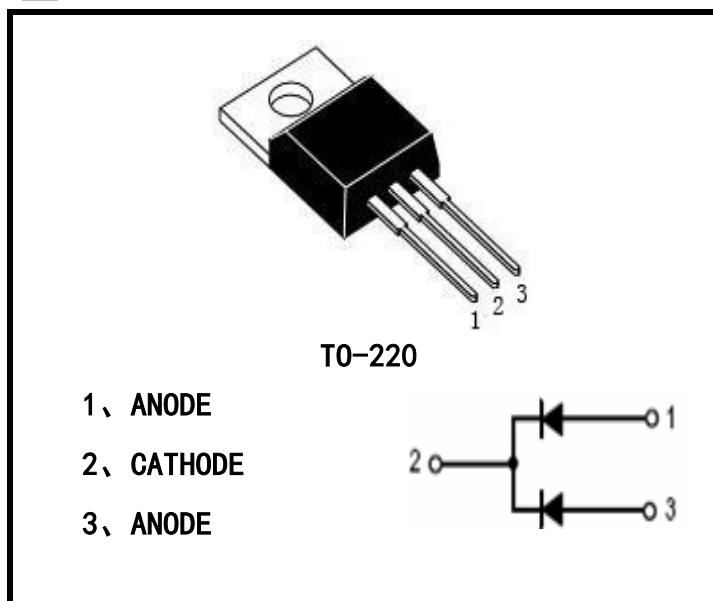


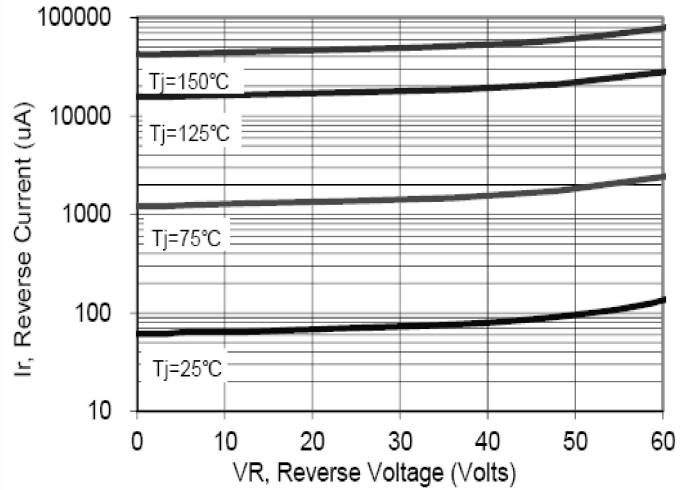
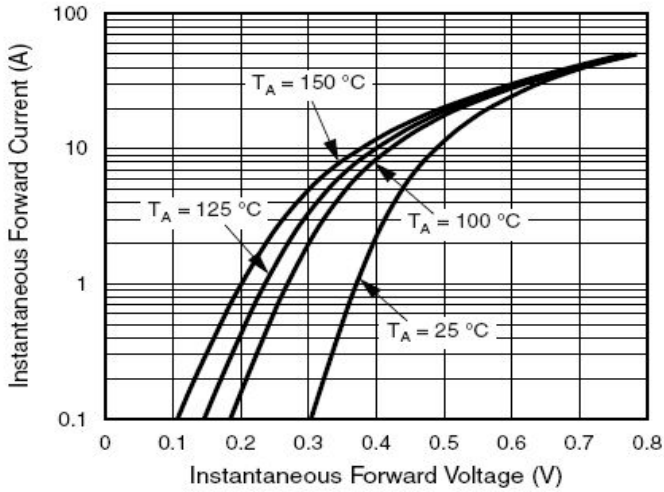
Ultra Low VF=0.4V at IF=5A
FEATURES

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

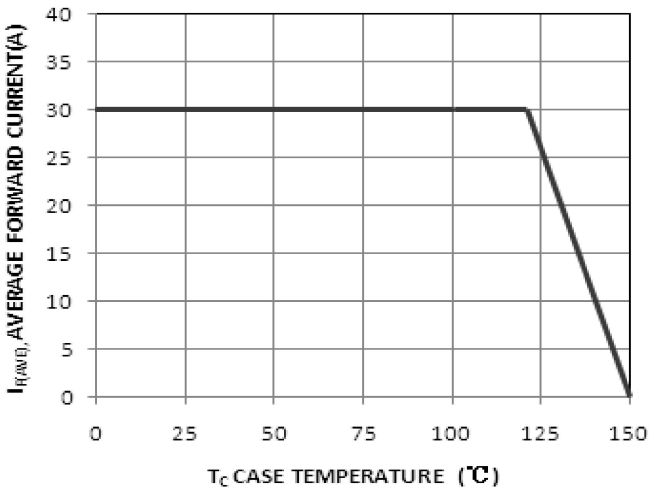
PACKAGE

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Output Current	$I_{F(per\ leg)}$	30	A
	$I_{F(Total)}$	60	
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I_{FSM}	400	A
Maximum Instantaneous Forward Voltage @IF=5A, TC=25°C @IF=30A, TC=25°C @IF=5A, TC=125°C @IF=30A, TC=125°C	V_F	0.4	V
		0.62	
		0.31	
		0.54	
Peak Reverse Current @Tc=25 °C at Rated DC Blocking Voltage @Tc=125°C	I_R	0.3	mA
50			
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C
Maximum Thermal Resistance	θ_{JC}	2	°C/W
	θ_{JA}	60	

Characteristics Curves



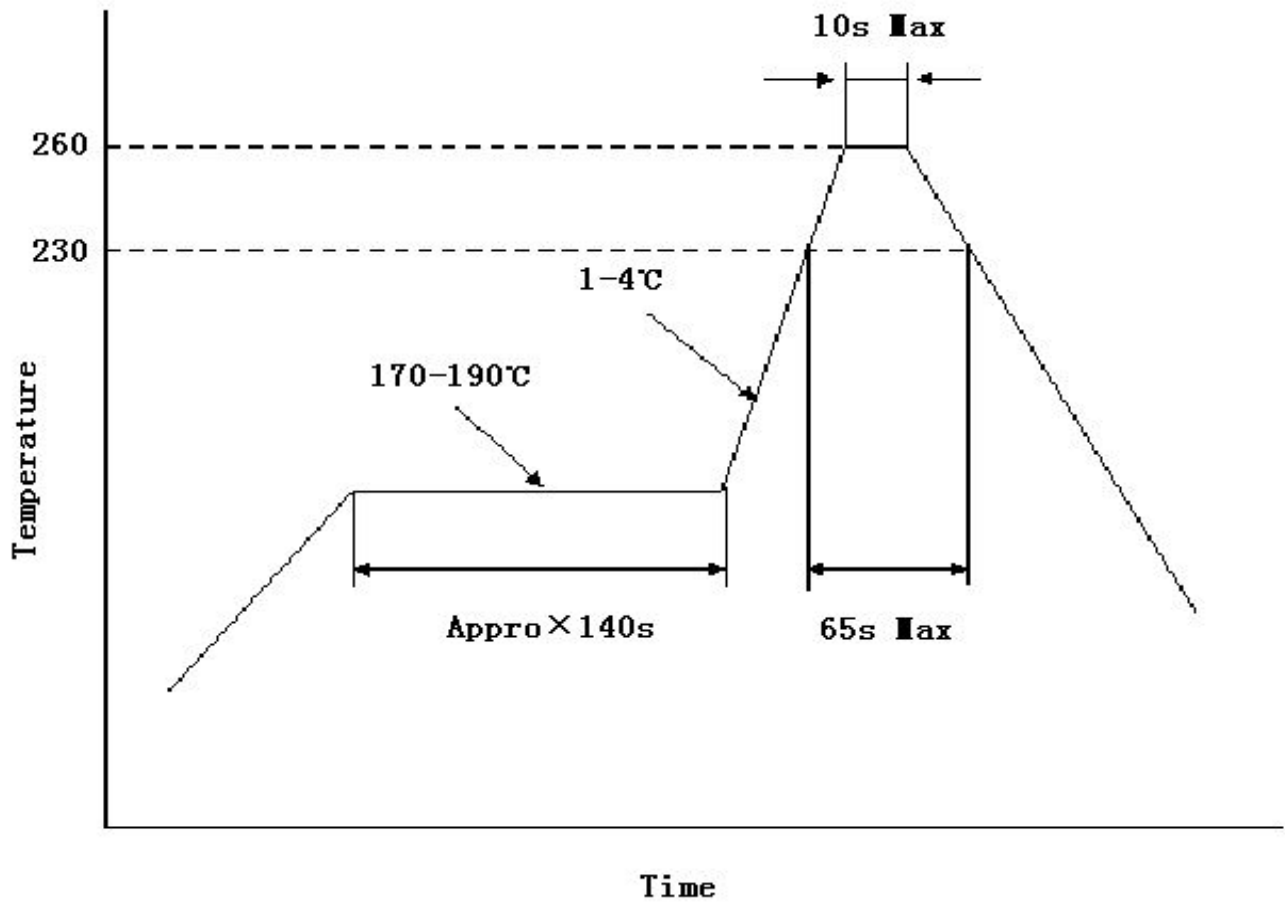
Typical Forward Voltage Per Diode



Typical Reverse Current Per Diode

Average Forward Current vs. Case Temperature Per Diode

■ Reflow Soldering Temperature Profile



T0-220 MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4		4.8	e	2.44	2.54	2.64
B	1.2		1.4	F	1.1		1.4
B1	1		1.4	L	12.5		14.5
b1	0.75		0.95	L1	3	3.5	4
c	0.4		0.55	ΦP	3.7	3.8	3.9
D	15		16.5	Q	2.5		3
D1	5.9		6.9	Q1	2		2.9
E	9.9		10.7				

